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August 2018

FDMA86265P

P-Channel PowerTrench[®] MOSFET -150 V, -1 A, 1.2 Ω

Features

- Max $r_{DS(on)} = 1.2 \Omega$ at $V_{GS} = -10 \text{ V}$, $I_D = -1 \text{ A}$
- Max $r_{DS(on)}$ = 1.4 Ω at V_{GS} = -6 V, I_D = -0.9 A
- Low Profile 0.8 mm maximum in the new package MicroFET 2x2 mm
- Very low RDS-on mid voltage P-channel silicon technology optimised for low Qg
- This product is optimised for fast switching applications as well as load switch applications
- 100% UIL tested
- RoHS Compliant

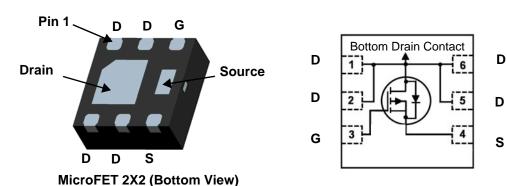


General Description

This P-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench® process that has been optimized for the on-state resistance and yet maintain superior switching performance.

Applications

- Active Clamp Switch
- Load Switch



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

| Symbol | Parame | | Ratings | Units | |
|--|--|------------------------|-----------|--------------|-----|
| V_{DS} | Drain to Source Voltage | | | -150 | V |
| V_{GS} | Gate to Source Voltage | | | ±25 | V |
| | Drain Current -Continuous | T _A = 25 °C | (Note 1a) | -1 | А |
| 'D | -Pulsed | | | -2 | _ A |
| E _{AS} | Single Pulse Avalanche Energy | | (Note 3) | 6 | mJ |
| D | Power Dissipation $T_A = 25 ^{\circ}\text{C}$ (Note | | (Note 1a) | 2.4 | W |
| P_D Power Dissipation $T_A = 25 ^{\circ}C$ | | (Note 1b) | 0.9 | VV | |
| T_J, T_{STG} | Operating and Storage Junction Tempera | ture Range | | -55 to + 150 | °C |

Thermal Characteristics

| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | (Note 1a) | 52 | °C/W |
|-----------------|---|-----------|-----|------|
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient | (Note 1b) | 145 | C/VV |

Package Marking and Ordering Information

| Device Marking | Device | Package | Reel Size | Tape Width | Quantity |
|----------------|------------|--------------|-----------|------------|------------|
| 265 | FDMA86265P | MicroFET 2X2 | 7 " | 12 mm | 3000 units |

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Тур | Max | Units |
|--------------------------------------|---|---|------|------|------|-------|
| Off Chara | cteristics | | | | | |
| BV _{DSS} | Drain to Source Breakdown Voltage | $I_D = -250 \mu A, V_{GS} = 0 V$ | -150 | | | V |
| $\frac{\Delta BV_{DSS}}{\Delta T_J}$ | Breakdown Voltage Temperature Coefficient | I _D = -250 μA, referenced to 25 °C -12 | | -125 | | mV/°C |
| I _{DSS} | Zero Gate Voltage Drain Current | V _{DS} = -120 V, V _{GS} = 0 V | | | -1 | μΑ |
| I _{GSS} | Gate to Source Leakage Current | $V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$ | | | ±100 | nA |

On Characteristics

| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS} = V_{DS}, I_{D} = -250 \mu A$ | -2 | -3.2 | -4 | V |
|--|--|--|------|------|-----|-------|
| $\frac{\Delta V_{GS(th)}}{\Delta T_J}$ | Gate to Source Threshold Voltage Temperature Coefficient | I_D = -250 μ A, referenced to 25 °C | | 5 | | mV/°C |
| | | $V_{GS} = -10 \text{ V}, I_D = -1 \text{ A}$ | | 0.86 | 1.2 | |
| r _{DS(on)} Static Drain to Source On Resistance | $V_{GS} = -6 \text{ V}, I_{D} = -0.9 \text{ A}$ | | 0.95 | 1.4 | Ω | |
| | $V_{GS} = -10 \text{ V}, I_D = -1 \text{ A}, T_J = 125 ^{\circ}\text{C}$ | | 1.53 | 2.2 | | |
| 9 _{FS} | Forward Transconductance | V _{DS} = -10 V, I _D = -1 A | | 1.9 | | S |

Dynamic Characteristics

| C _{iss} | Input Capacitance | V 75.V.V 0.V | | 158 | 210 | pF |
|------------------|------------------------------|---|-----|-----|-----|----|
| Coss | Output Capacitance | $V_{DS} = -75 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$ | | 16 | 25 | pF |
| C _{rss} | Reverse Transfer Capacitance | 1 - 1 1/11/12 | | 0.7 | 5 | pF |
| R_q | Gate Resistance | | 0.1 | 3 | 7.5 | Ω |

Switching Characteristics

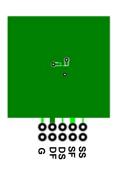
| t _{d(on)} | Turn-On Delay Time | | | 5.8 | 12 | ns |
|---------------------|-------------------------------|--|--|-----|----|----|
| t _r | Rise Time | V _{DD} = -75 V, I _D = -1 A, | | 2.2 | 10 | ns |
| t _{d(off)} | Turn-Off Delay Time | $V_{GS} = -10 \text{ V}, R_{GEN} = 6 \Omega$ | | 8 | 16 | ns |
| t _f | Fall Time | | | 6.4 | 13 | ns |
| $Q_{g(TOT)}$ | Total Gate Charge | $V_{GS} = 0 \text{ V to -10 V } V_{DD} = -75 \text{ V},$ | | 2.8 | 4 | nC |
| Q _{gs} | Total Gate Charge | I _D = -1 A | | 0.8 | | nC |
| Q _{gd} | Gate to Drain "Miller" Charge | | | 0.7 | | nC |

Drain-Source Diode Characteristics

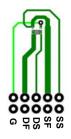
| V_{SD} | Source to Drain Diode Forward Voltage | $V_{GS} = 0 \text{ V}, I_{S} = -1 \text{ A}$ | (Note 2) | | -0.87 | -1.3 | V |
|-----------------|---------------------------------------|--|----------|----|-------|------|----|
| t _{rr} | Reverse Recovery Time | I _F = -1 A, di/dt = 100 A/μs | | | 50 | 80 | ns |
| Q _{rr} | Reverse Recovery Charge | | | 78 | 124 | nC | |

NOTES

^{1.} R_{0,1A} is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R_{0,1C} is guaranteed by design while R_{0,CA} is determined by the user's board design.



a. 52 °C/W when mounted on a 1 in² pad of 2 oz copper.



b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

- 2. Pulse Test: Pulse Width < 300 $\mu\text{s},$ Duty cycle < 2.0%.
- 3. Starting T $_{J}$ = 25 °C; P-ch: L =3 mH, I $_{AS}$ = -2 A, V $_{DD}$ = -150 V, V $_{GS}$ = -10 V.

Typical Characteristics T_J = 25 °C unless otherwise noted

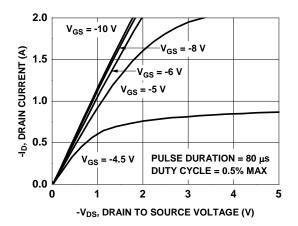
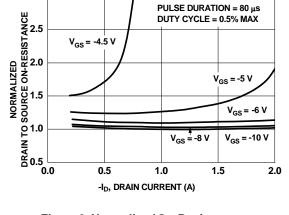


Figure 1. On Region Characteristics



3.0

Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

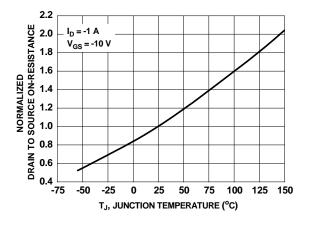


Figure 3. Normalized On Resistance vs Junction Temperature

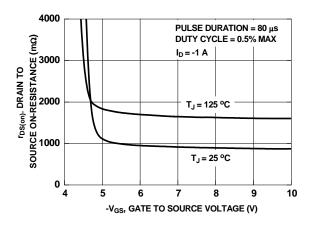


Figure 4. On-Resistance vs Gate to Source Voltage

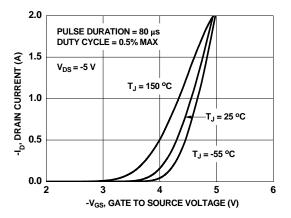


Figure 5. Transfer Characteristics

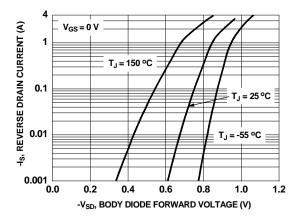


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics $T_J = 25$ °C unless otherwise noted

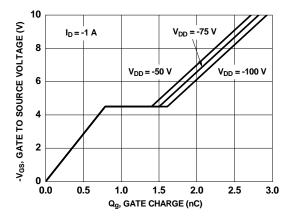


Figure 7. Gate Charge Characteristics

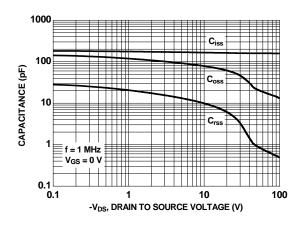


Figure 8. Capacitance vs Drain to Source Voltage

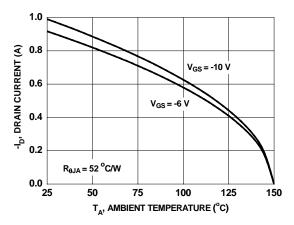


Figure 9. Maximum Continuous Drain Current vs Ambient Temperature

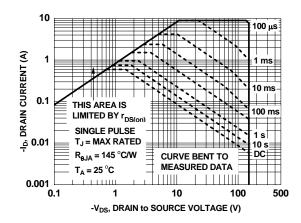


Figure 10. Forward Bias Safe Operating Area

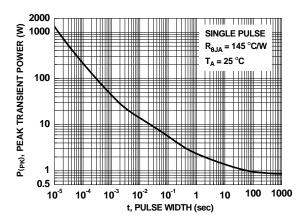


Figure 11. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25$ °C unless otherwise noted

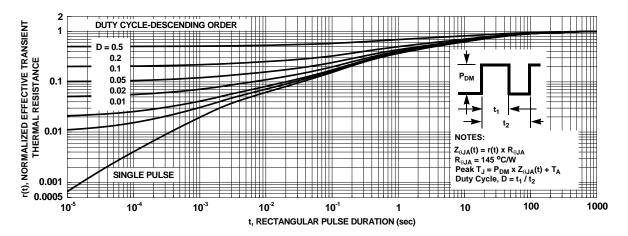
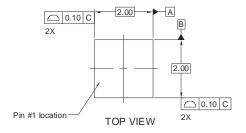
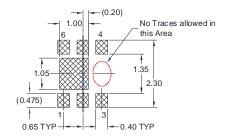


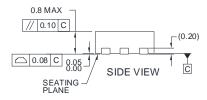
Figure 12. Junction-to-Ambient Transient Thermal Response Curve

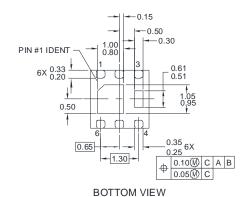
Dimensional Outline and Pad Layout

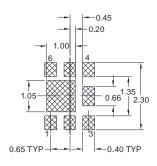




RECOMMENDED LAND PATTERN OPT 1







RECOMMENDED LAND PATTERN OPT 2

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